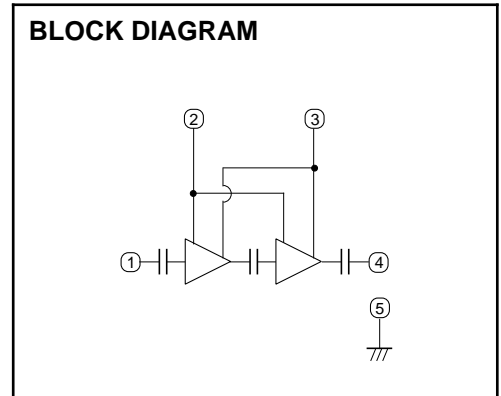
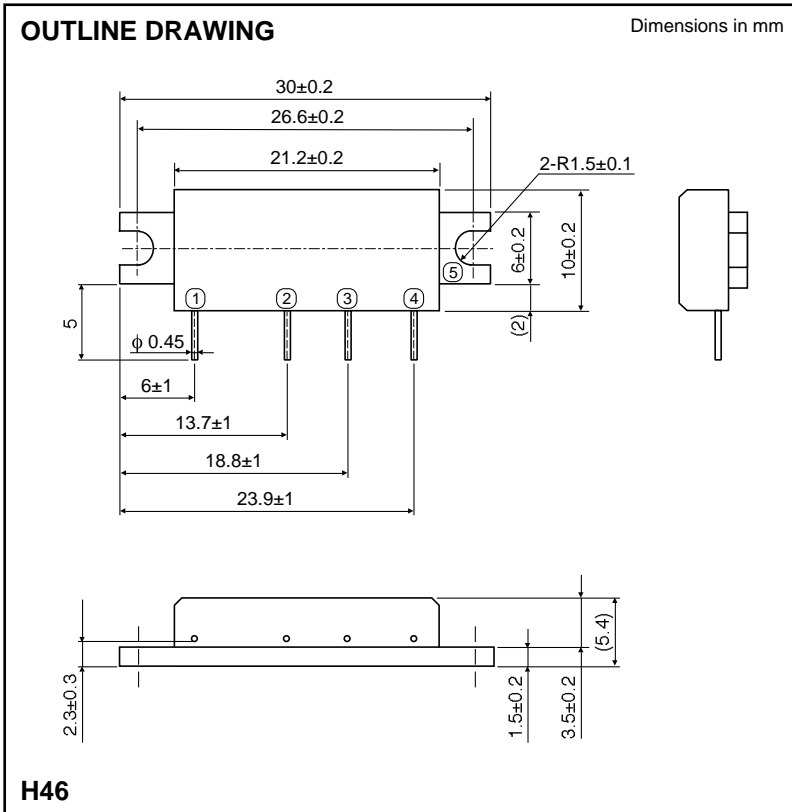


MITSUBISHI RF POWER MODULE  
**M68710TL**

SILICON MOS FET POWER AMPLIFIER, 330-360MHz, 2W, FM PORTABLE RADIO



- PIN:  
 ① Pin : RF INPUT  
 ② VGG : GATE BIAS SUPPLY  
 ③ VDD : DRAIN BIAS SUPPLY  
 ④ PO : RF OUTPUT  
 ⑤ GND: FIN

**ABSOLUTE MAXIMUM RATINGS** (Tc=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Ratings	Unit
VDD	Supply voltage	VGG 3.5V, ZG=ZL=50	9	V
VGG	Gate bias voltage		4	V
Pin	Input power	f=330-360MHz, ZG=ZL=50	30	mW
Po	Output power	f=330-360MHz, VDD 9V, ZG=ZL=50	3	W
Tc (OP)	Operation case temperature	f=330-360MHz, VDD 9V, ZG=ZL=50	-30 to +110	°C
Tstg	Storage temperature		-40 to +110	°C

Note. Above parameters are guaranteed independently.

**ELECTRICAL CHARACTERISTICS** (Tc=25°C, ZG=ZL=50 unless otherwise noted)

Symbol	Parameter	Test conditions	Limits		Unit
			Min	Max	
f	Frequency range		330	360	MHz
Po	Output power		2		W
T	Total efficiency	VDD=6V, VGG=3.5V, Pin=20mW	40		%
2fo	2nd. harmonic			-25	dBc
in	Input VSWR			4	-
-	Stability	ZG=50, VDD=4-8V, Load VSWR<4:1	No parasitic oscillation		-
-	Load VSWR tolerance	VDD=9V, Pin=20mW, PO=2W (VGG adjust), ZL=20:1	No degradation or destroy		-

Note. Above parameters, ratings, limits and test conditions are subject to change.